N-Channel Super Junction Power MOSFET Ⅳ

General Description

The series of devices use advanced trench gate super junction technology and design to provide ultra-low $R_{DS(ON)}$ and low gate charge and With a rapid recovery body diode.This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, industrial power applications,Fast charger, new energy vehicle charging pile, on-board OBC etc.

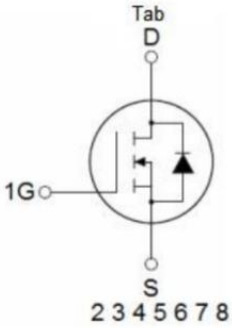
Features

- New technology for high voltage device
- Ultra low on-resistance and ultra low conduction losses
- Ultra Low Gate Charge cause lower driving requirements
- Diode reverse recovery speed is super fast
- High reliability
- ROHS compliant&Halogen Free

Application

- Power factor correction（PFC）
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply（UPS）
- On-board charger(OBC)

$V_{DS\ min@Tjmax}$	710	V
$R_{DS(ON)TYP}$	110	mΩ
ID	26	A
Qg	41	nC



Schematic diagram

✧ **Intrinsic fast-recovery body diode**

Package Marking And Ordering Information

Device	Device Package	Marking
NCE65NF130LL	TOLL-8L	NCE65NF130LL

TOLL-8L

Table 1. Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS}=0V）	V_{DS}	650	V
Gate-Source Voltage (V_{DS}=0V) AC (f>1 Hz)	V_{GS}	±30	V
Gate-Source Voltage (V_{DS}=0V) DC	V_{GS}	±20	V
Continuous Drain Current at Tc=25°C	$I_{D\ (DC)}$	26	A
Continuous Drain Current at Tc=100°C	$I_{D\ (DC)}$	18.2	A
Pulsed drain current **(Note 1)**	$I_{DM\ (pluse)}$	78	A
Maximum Power Dissipation(Tc=25℃) Derate above 25°C	P_D	237 1.58	W W/°C
Avalanche current**(Note 1)**	I_{AS}	7	A
Drain Source voltage slope, V_{DS} ≤480 V,	dv/dt	50	V/ns
Reverse diode dv/dt， V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+175	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	0.63	°C /W
Thermal Resistance，Junction-to-Ambient （Maximum）	R_{thJA}	62	°C /W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250uA	650			V
Zero Gate Voltage Drain Current(Tc=25℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V			10	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V			400	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=500uA	3.5	4.2	5.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=13A		110	130	mΩ
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz		2161		pF
Output Capacitance	C_{oss}			95		pF
Reverse Transfer Capacitance	C_{rss}			50		pF
Total Gate Charge	Q_g	V_{DS}=480V,I_D=13A, V_{GS}=10V		41.2		nC
Gate-Source Charge	Q_{gs}			16.3		nC
Gate-Drain Charge	Q_{gd}			12.8		nC
Gate plateau voltage	Vgp			7.0		V
Intrinsic gate resistance	R_G	f = 1 MHz open drain		1.5		Ω
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=380V,I_D=13A, R_G=1.7Ω,V_{GS}=10V		43		nS
Turn-on Rise Time	t_r			16		nS
Turn-Off Delay Time	$t_{d(off)}$			93		nS
Turn-Off Fall Time	t_f			20		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	T_C=25°C			26	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				78	A
Forward On Voltage	V_{SD}	Tj=25°C,I_{SD}=26A,V_{GS}=0V		1.0	1.2	V
Reverse Recovery Time	t_{rr}	Tj=25°C,I_F=13A,di/dt=100A/μs		145		nS
Reverse Recovery Charge	Q_{rr}			0.725		uC
Peak Reverse Recovery Current	I_{rrm}			10		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25℃,VDD=50V,VG=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

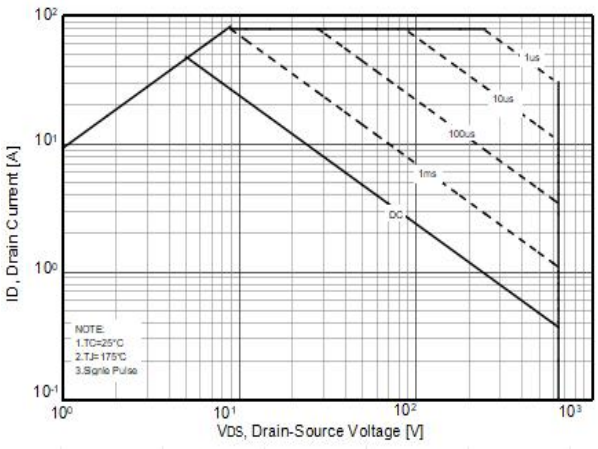


Figure2. Capacitance

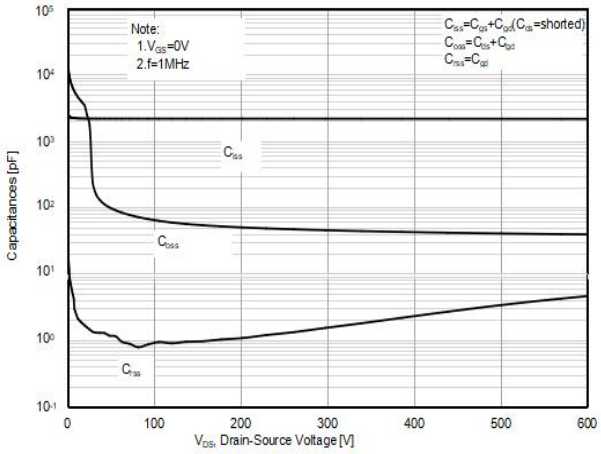


Figure3. Output characteristics

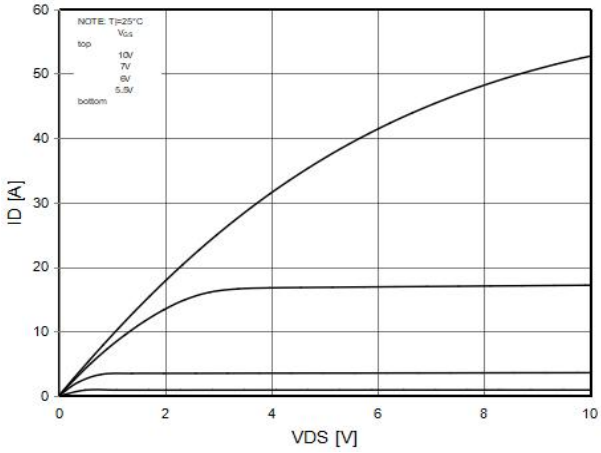


Figure4. Source-Drain Diode Forward Voltage

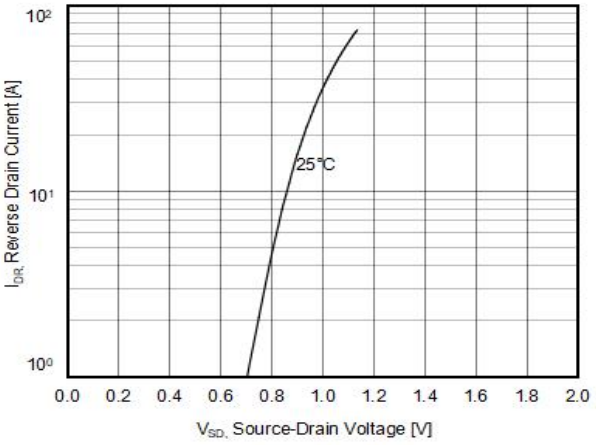


Figure5. Static drain-source on resistance

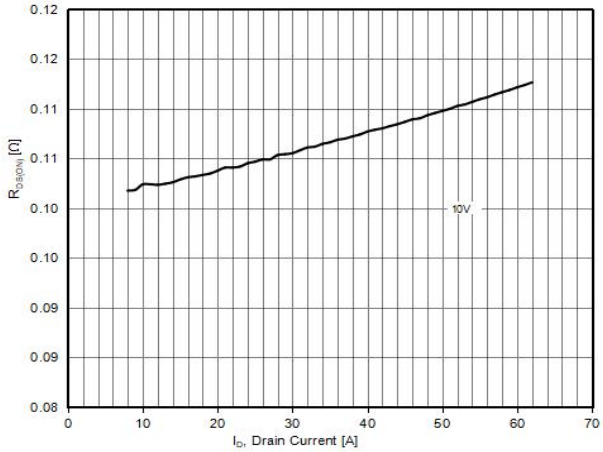


Figure6. Transfer characteristics

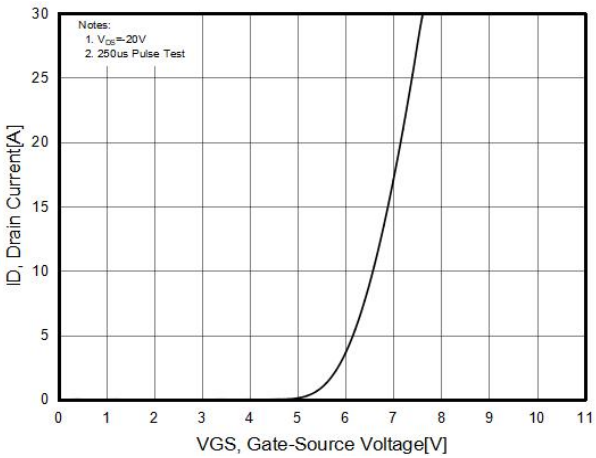


Figure7. $R_{DS(ON)}$ vs Junction Temperature

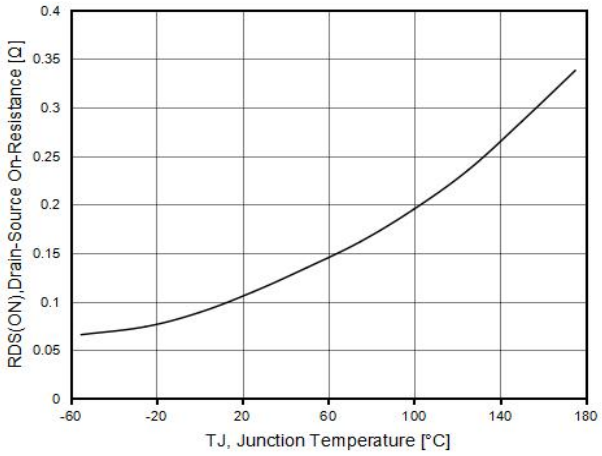


Figure8. BV_{DSS} vs Junction Temperature

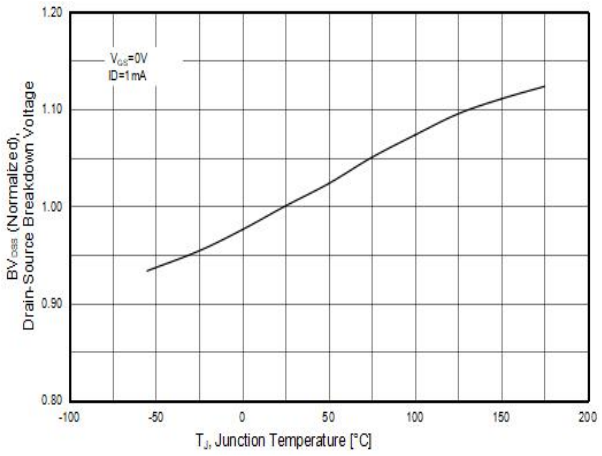


Figure9. Gate charge waveforms

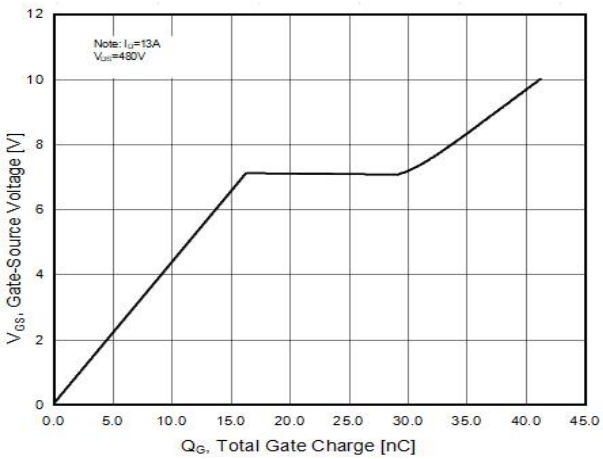
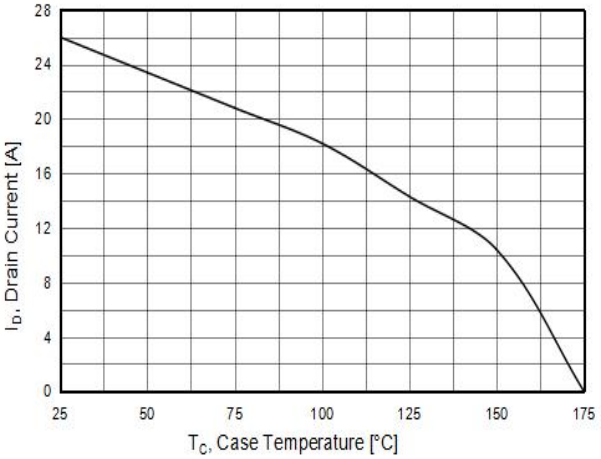
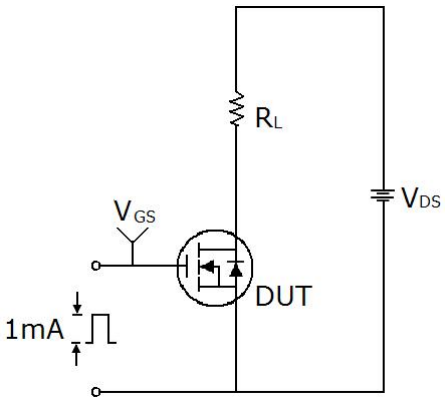


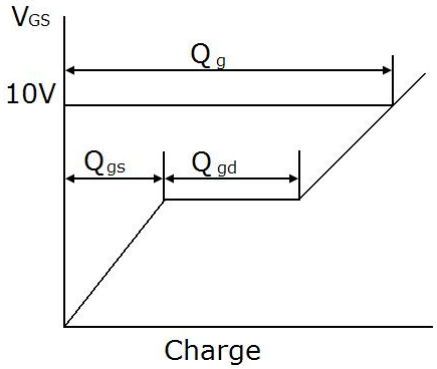
Figure10. Maximum I_D vs Junction Temperature



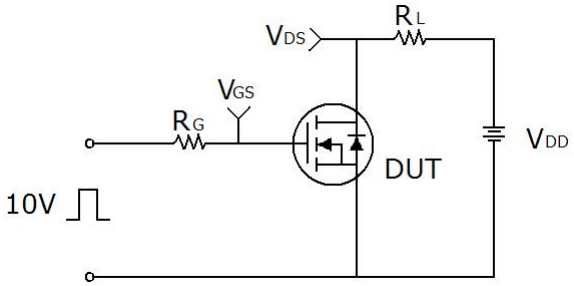
Test circuit

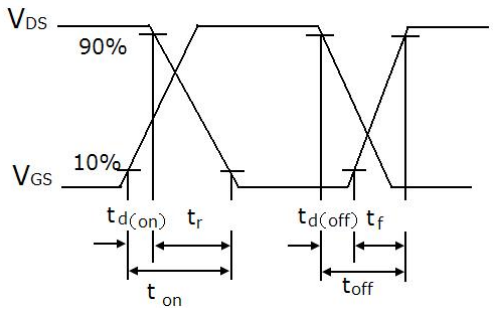
1）Gate charge test circuit & Waveform



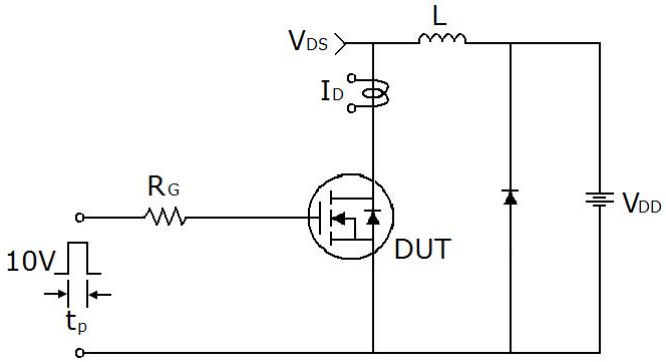


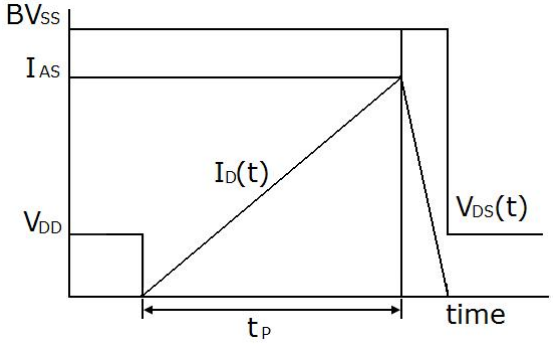
2）Switch Time Test Circuit：



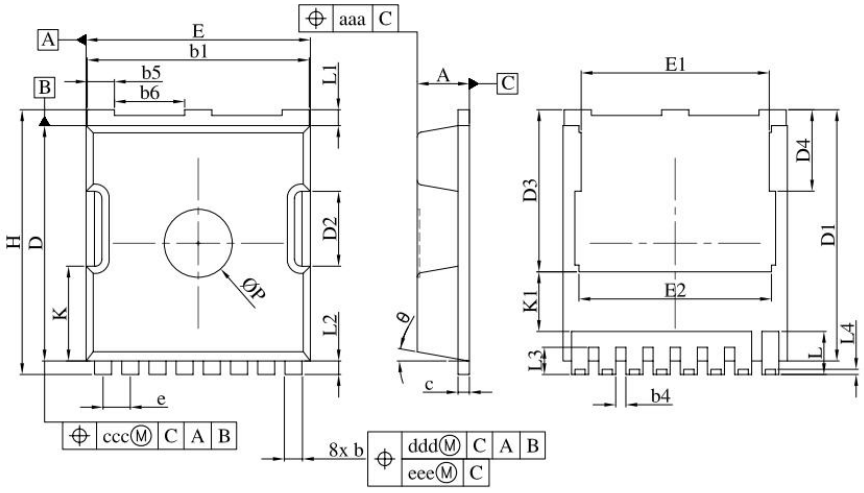


3）Unclamped Inductive Switching Test Circuit & Waveforms





TOLL-8L Package Information



SYMBOL	Dimensions In Millimeters			Dimensions In Inches		
	Min	Typ	Max	Min	Typ	Max
A	2.20	2.30	2.40	0.087	0.091	0.094
b	0.70	0.80	0.90	0.028	0.031	0.035
b1	9.70	9.80	9.90	0.382	0.386	0.390
b4	0.30	0.40	0.50	0.012	0.016	0.020
b5	1.10	1.20	1.30	0.043	0.047	0.051
b6	3.00	3.10	3.20	0.118	0.122	0.126
c	0.40	0.50	0.60	0.016	0.020	0.024
D	10.28	10.38	10.55	0.405	0.409	0.415
D1	10.98	11.08	11.18	0.432	0.436	0.440
D2	3.20	3.30	3.40	0.126	0.130	0.134
D3	7.00	7.15	7.30	0.276	0.281	0.287
D4	3.44	3.59	3.74	0.135	0.141	0.147
e	1.10	1.20	1.30	0.043	0.047	0.051
E	9.80	9.90	10.00	0.386	0.390	0.394
E1	8.20	8.30	8.40	0.323	0.327	0.331
E2	8.35	8.50	8.65	0.329	0.335	0.341
H	11.50	11.68	11.85	0.453	0.460	0.467
K	4.08	4.18	4.28	0.161	0.165	0.169
K1	2.45	--	--	0.096	--	--
L	1.60	1.90	2.10	0.063	0.075	0.083
L1	0.50	0.70	0.90	0.020	0.028	0.035
L2	0.50	0.60	0.70	0.020	0.024	0.028
L3	1.00	1.20	1.30	0.039	0.047	0.051
L4	0.13	0.23	0.33	0.005	0.009	0.013
P	2.85	3.00	3.15	0.112	0.118	0.124

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